# NST856BF3T5G

# PNP General Purpose Transistor

The NST856BF3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563/SOT-963 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

#### **Features**

- h<sub>FE</sub>, 220-475
- Low  $V_{CE(sat)}$ ,  $\leq -0.3 \text{ V}$
- Reduces Board Space
- This is a Halide-Free Device
- This is a Pb-Free Device

### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	$V_{CEO}$	-65	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	-80	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current – Continuous	Ic	-100	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub> (Note 1)	290 2.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 1)	432	°C/W
Total Device Dissipation, T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub> (Note 2)	347 2.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 2)	360	°C/W
Thermal Resistance, Junction-to-Lead 3	R <sub>ΨJL</sub> (Note 2)	143	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

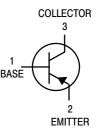
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. 100 mm<sup>2</sup> 1 oz, copper traces.
- 2. 500 mm<sup>2</sup> 1 oz, copper traces.



# ON Semiconductor®

http://onsemi.com



NST856BF3T5G



SOT-1123 CASE 524AA STYLE 1

### **MARKING DIAGRAM**



A = Device Code
M = Date Code

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NST856BF3T5G	SOT-1123 (Pb-Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# NST856BF3T5G

## **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage (I <sub>C</sub> = -10 mA)	V <sub>(BR)CEO</sub>	-65	-	-	٧
Collector - Emitter Breakdown Voltage (I <sub>C</sub> = -10 μA, V <sub>EB</sub> = 0)	V <sub>(BR)CES</sub>	-80	-	-	٧
Collector – Base Breakdown Voltage (I <sub>C</sub> = -10 μA)	V <sub>(BR)CBO</sub>	-80	-	-	٧
Emitter – Base Breakdown Voltage (I <sub>E</sub> = -1.0 μA)	V <sub>(BR)EBO</sub>	-5.0	-	-	V
Collector Cutoff Current ( $V_{CB} = -30 \text{ V}$ ) ( $V_{CB} = -30 \text{ V}$ , $T_A = 150^{\circ}\text{C}$ )	Ісво	- -	- -	-15 -4.0	nA μA
ON CHARACTERISTICS					
DC Current Gain $ \begin{array}{l} (I_C = -10 \; \mu A, \; V_{CE} = -5.0 \; V) \\ (I_C = -2.0 \; mA, \; V_{CE} = -5.0 \; V) \end{array} $	h <sub>FE</sub>	- 220	150 290	- 475	_
Collector – Emitter Saturation Voltage ( $I_C = -10$ mA, $I_B = -0.5$ mA) ( $I_C = -100$ mA, $I_B = -5.0$ mA)	V <sub>CE(sat)</sub>	_ _	- -	-0.3 -0.8	V
Base – Emitter Saturation Voltage ( $I_C = -10$ mA, $I_B = -0.5$ mA) ( $I_C = -100$ mA, $I_B = -5.0$ mA)	V <sub>BE(sat)</sub>	- -	-0.7 -0.9	- -	V
Base – Emitter On Voltage (I <sub>C</sub> = -2.0 mA, V <sub>CE</sub> = -5.0 V) (I <sub>C</sub> = -10 mA, V <sub>CE</sub> = -5.0 V)	V <sub>BE(on)</sub>	-0.6 -	- -	-0.75 -0.82	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product ( $I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ MHz}$ )	f⊤	100	_	_	MHz
Output Capacitance (V <sub>CB</sub> = -10 V, f = 1.0 MHz)	C <sub>obo</sub>	-	-	4.5	pF
Input Capacitance (V <sub>EB</sub> = -0.5 V, I <sub>C</sub> = 0 mA, f = 1.0 MHz)	C <sub>ibo</sub>	-	_	10	pF
Noise Figure (I <sub>C</sub> = $-0.2$ mA, V <sub>CE</sub> = $-5.0$ Vdc, R <sub>S</sub> = $2.0$ k $\Omega$ , f = $1.0$ kHz, BW = $200$ Hz)	NF	-	_	10	dB

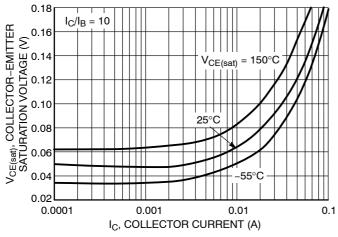


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

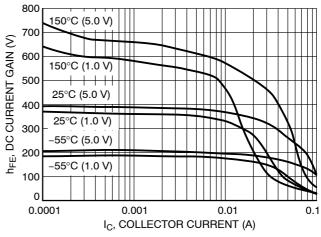


Figure 2. DC Current Gain vs. Collector Current

### NST856BF3T5G

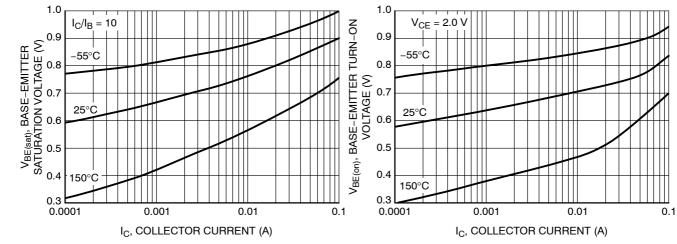


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base Emitter Turn-On Voltage vs.
Collector Current

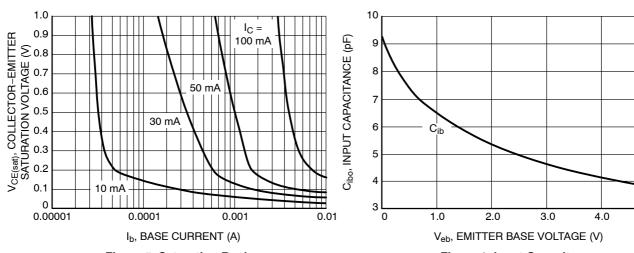


Figure 5. Saturation Region

Figure 6. Input Capacitance

5.0

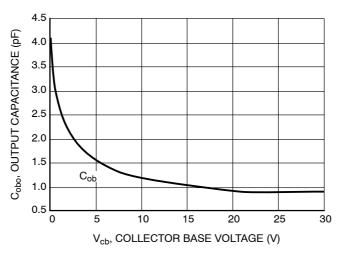


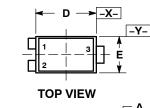
Figure 7. Output Capacitance

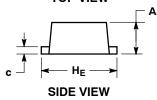


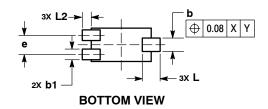
SOT-1123 CASE 524AA ISSUE C

**DATE 29 NOV 2011** 

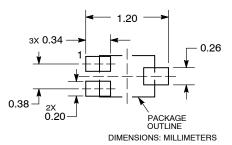
#### SCALE 8:1







### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF BASE MATERIAL.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD
  FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.34	0.40		
b	0.15	0.28		
b1	0.10	0.20		
c	0.07	0.17		
D	0.75	0.85		
Е	0.55	0.65		
е	0.35	0.40		
HE	0.95	1.05		
L	0.185 REF			
L2	0.05 0.1			

### **GENERIC MARKING DIAGRAM\***



= Specific Device Code Μ = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	<ol><li>SOURCE</li></ol>
3. COLLECTOR	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	3. DRAIN

DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-1123, 3-LEAD, 1.0X0.6X0.37, 0.35P		PAGE 1 OF 1	

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales